- Inputs Are TTL-Voltage Compatible
- EPIC[™] (Enhanced-Performance Implanted CMOS) Process
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) 300-mil DIPs

description

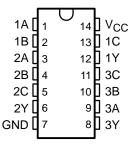
These devices contain three independent 3-input NAND gates. They perform the Boolean function $Y = \overline{A} \cdot \overline{B} \cdot \overline{C}$ or $Y = \overline{A} + \overline{B} + \overline{C}$ in positive logic.

The SN54AHCT10 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74AHCT10 is characterized for operation from –40°C to 85°C.

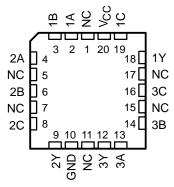
FUNCTION TABLE (each gate)

	INPUTS		OUTPUT
Α	В	С	Υ
Н	Н	Н	L
L	X	Χ	Н
Х	L	Χ	Н
Х	X	L	Н

SN54AHCT10 . . . J OR W PACKAGE SN74AHCT10 . . . D, DB, N, OR PW PACKAGE (TOP VIEW)

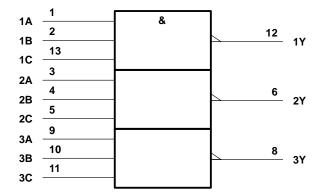


SN54AHCT10 . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the D, DB, J, N, PW, and W packages.

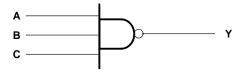


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logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}		
Input voltage range, V _I (see Note 1)		
Output voltage range, VO (see Note 1)		-0.5 V to V _{CC} + 0.5 V
Input clamp current, I_{IK} ($V_I < 0$)		–20 mA
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CO}$	c)	±20 mA
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$		±25 mA
Continuous current through V _{CC} or GND		
Package thermal impedance, θ _{.IA} (see Note 2)): D package	127°C/W
, 0,11	DB package	158°C/W
	N package	78°C/W
	PW package	170°C/W
Storage temperature range, T _{stq}		

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with JESD 51, except for through-hole packages, which use a trace length of zero.

recommended operating conditions (see Note 3)

		SN54AHCT10		SN74AI	HCT10	UNIT
		MIN	MAX	MIN	MAX	UNIT
Vсс	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2		2		V
V _{IL}	Low-level input voltage		0.8		0.8	V
٧ _I	Input voltage	0	5.5	0	5.5	V
Vo	Output voltage	0	VCC	0	VCC	V
ЮН	High-level output current		-8		-8	mA
loL	Low-level output current		8		8	mA
Δt/Δν	Input transition rise or fall rate		20		20	ns/V
T _A	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: Unused inputs must be held high or low to prevent them from floating.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V	T _A = 25°C		SN54AHCT10		SN74AHCT10		UNIT	
PARAMETER	TEST CONDITIONS	VCC	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
Vo.,	I _{OH} = -50 μA		4.4	4.5		4.4		4.4		V
Voн	$I_{OH} = -8 \text{ mA}$	4.5 V	3.94			3.8		3.8		٧
Vo.	I _{OL} = 50 μA	4.5 V			0.1		0.1		0.1	V
VOL	I _{OL} = 8 mA	4.5 V			0.36		0.44		0.44	
lį	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1		±1	μΑ
lcc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20		20	μΑ
ΔICC [†]	One input at 3.4 V, Other inputs at V _{CC} or GND	5.5 V			1.35		1.5		1.5	mA
C _i	V _I = V _{CC} or GND	5 V		2	10				10	pF

[†] This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

					SN	54AHCT	10				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T _A = 25°C			MIN	MAY	UNIT		
				MIN	TYP	MAX	IVIIIN	MAX			
^t PLH*	A D or C	Y	Y C _L =	A, B, or C Y C _L = 15 pF	C: -15 pF		3.9	5.9	1	7	20
^t PHL*	A, B, OI C				1		3.9	5.9	1	7	ns
^t PLH	A, B, or C	V	C: -50 pE		5.4	7.9	1	9	ns		
^t PHL	A, B, 01 C	1	C _L = 50 pF		5.4	7.9	1	9	115		

^{*} On products compliant to MIL-PRF-38535, this parameter is ensured but not production tested.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

				SN74AHCT10						
PARAMETER	FROM (INPUT)	TO (OUTPUT)		T _A = 25°C			MIN	44 A V	UNIT	
	((0011 01)		MIN	TYP	MAX	IVIIIV	MAX		
^t PLH	A, B, or C	Y	V	C: -15 nF		3.9	5.9	1	7	20
t _{PHL}	A, B, Of C		$C_L = 15 pF$		3.9	5.9	1	7	ns	
^t PLH	A, B, or C	V	C: - 50 pF		5.4	7.9	1	9	20	
tPHL	A, B, OI C	T	C _L = 50 pF		5.4	7.9	1	9	ns	

noise characteristics, $V_{CC} = 5 \text{ V}$, $C_L = 50 \text{ pF}$, $T_A = 25^{\circ}\text{C}$ (see Note 4)

	PARAMETER	SN74AHCT10			
	PARAMETER	MIN	TYP MAX 0.8 -0.8	UNIT	
VOL(P)	Quiet output, maximum dynamic V _{OL}			0.8	V
V _{OL} (V)	Quiet output, minimum dynamic V _{OL}			-0.8	V
VOH(V)	Quiet output, minimum dynamic VOH				٧
V _{IH(D)}	High-level dynamic input voltage	2			V
VIL(D)	Low-level dynamic input voltage			0.8	V

NOTE 4: Characteristics are determined during product characterization and ensured by design for surface-mount packages only.



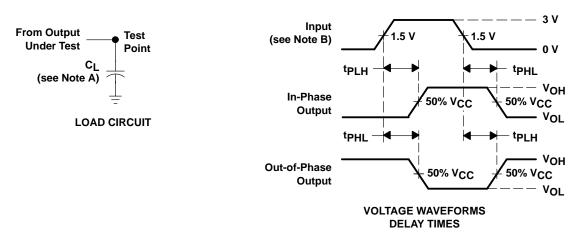
SN54AHCT10, SN74AHCT10 TRIPLE 3-INPUT POSITIVE-NAND GATES

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operating characteristics, $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST CO	ONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	14	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_f = 3 ns, t_f = 3 ns.
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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